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(54) **METHOD FOR MANUFACTURING  
CAPACITOR ARRAY, CAPACITOR ARRAY,  
AND SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

A method for manufacturing a capacitor array includes: providing a substrate provided with a device area configured for forming a capacitor and a peripheral area located at a periphery of the device area; forming successively a first support layer and a first sacrificial layer on the substrate; etching the first sacrificial layer of the peripheral area to expose the first support layer, so as to form a first via; and filling the first via to form a support pillar.

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